



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

MCH6341 — P-Channel Silicon MOSFET — General-Purpose Switching Device Applications

Features

- Low ON-resistance
- Halogen free compliance
- 4V drive
- Protection diode in

Specifications

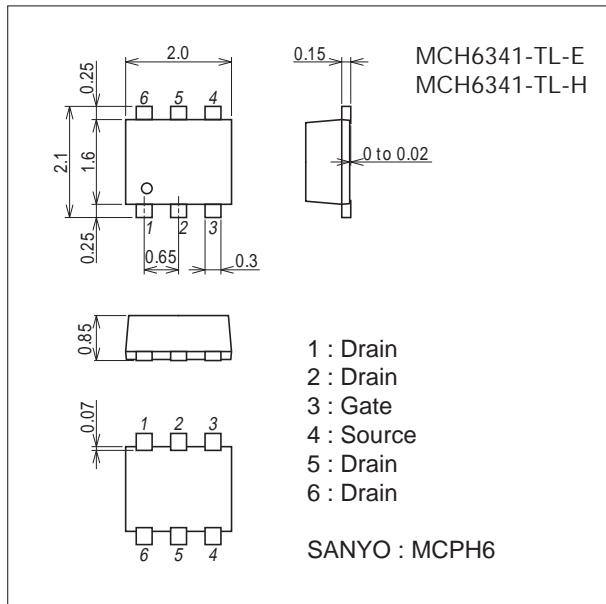
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-5	A
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-20	A
Allowable Power Dissipation	PD	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ)

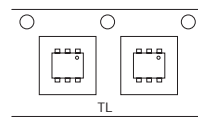
7022A-009



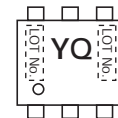
Product & Package Information

- Package : MCPH6
- JEITA, JEDEC : SC-88, SC-70-6, SOT-363
- Minimum Packing Quantity : 3,000 pcs./reel

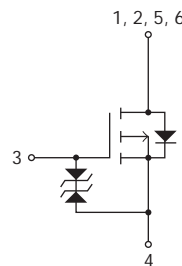
Packing Type : TL



Marking



Electrical Connection

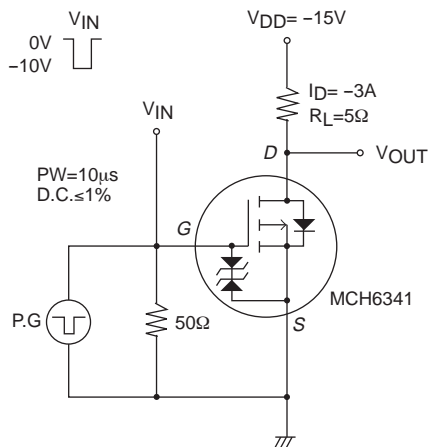


MCH6341

Electrical Characteristics at Ta=25°C

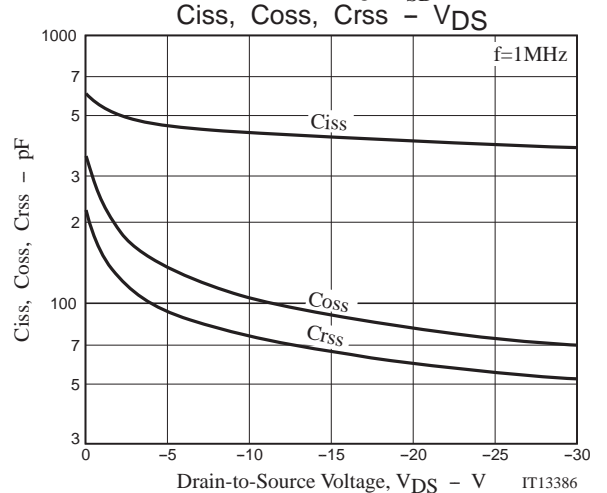
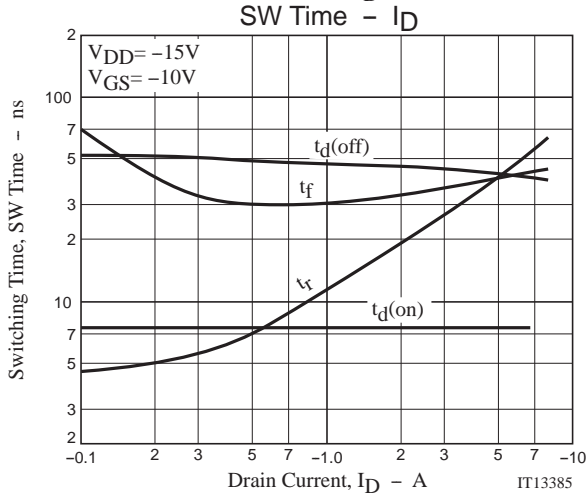
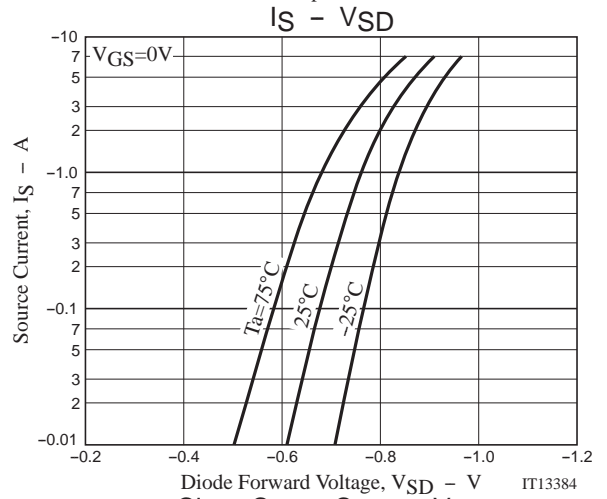
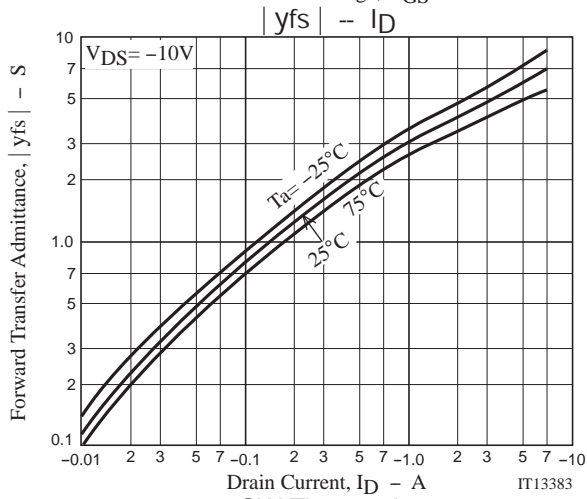
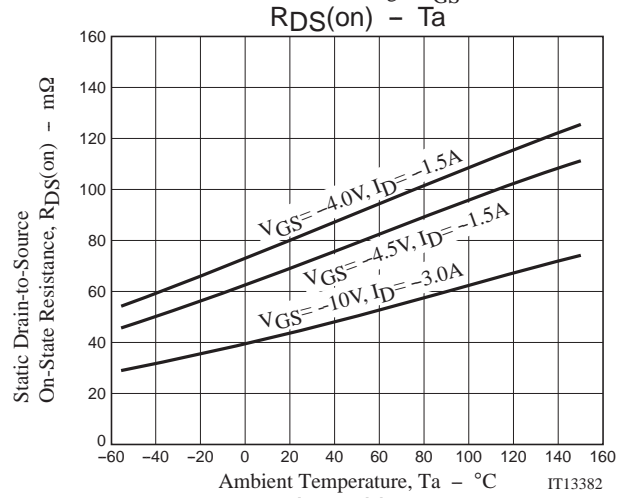
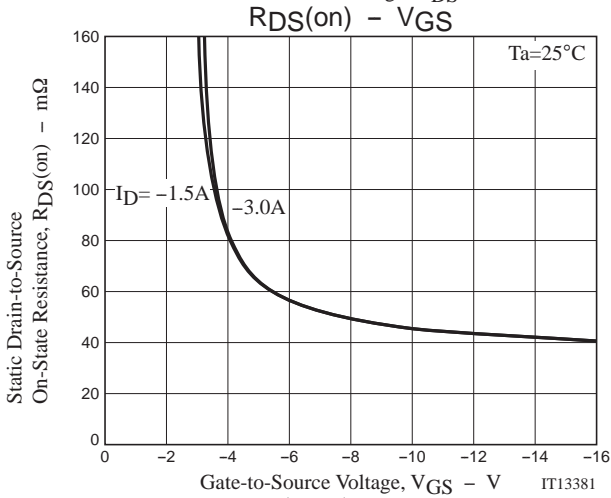
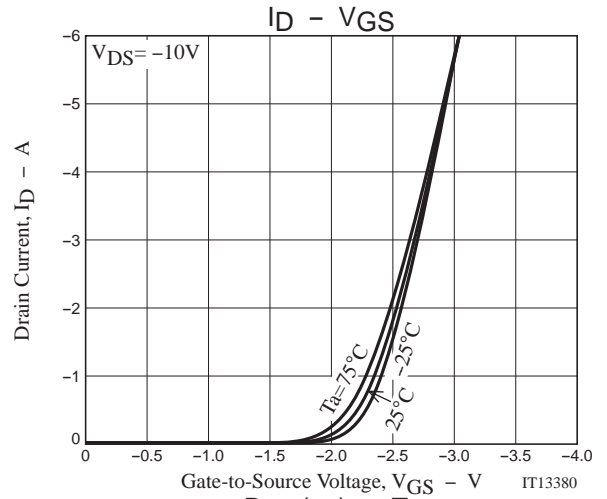
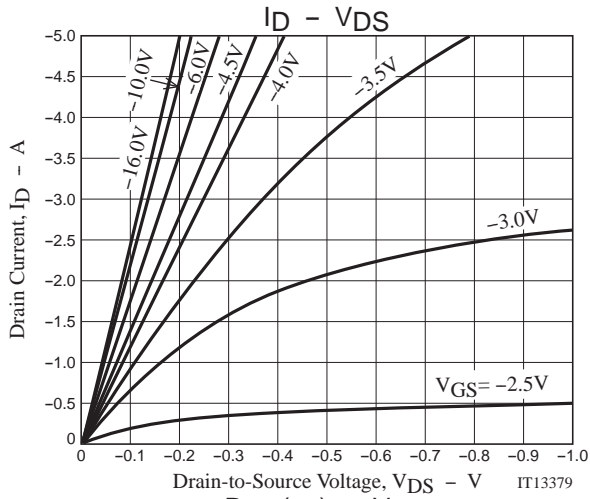
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-3A	2.8	4.8		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-3A, V _{GS} =-10V		45	59	mΩ
	R _{DS(on)2}	I _D =-1.5A, V _{GS} =-4.5V		71	100	mΩ
	R _{DS(on)3}	I _D =-1.5A, V _{GS} =-4V		82	115	mΩ
Input Capacitance	C _{iss}			430		pF
Output Capacitance	C _{oss}	V _{DS} =-10V, f=1MHz		105		pF
Reverse Transfer Capacitance	C _{rss}			75		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		7.5		ns
Rise Time	t _r			26		ns
Turn-OFF Delay Time	t _{d(off)}			45		ns
Fall Time	t _f			35		ns
Total Gate Charge	Q _g				10	
Gate-to-Source Charge	Q _{gs}	V _{DS} =-15V, V _{GS} =-10V, I _D =-5A		2.0		nC
Gate-to-Drain "Miller" Charge	Q _{gd}			2.5		nC
Diode Forward Voltage	V _{SD}		I _S =-5A, V _{GS} =0V		-0.87	-1.5

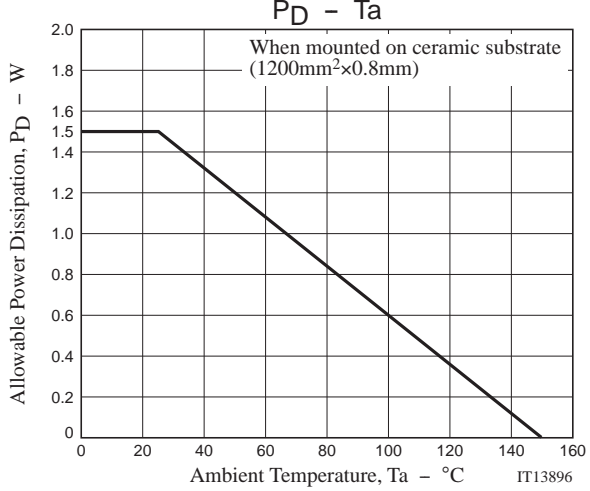
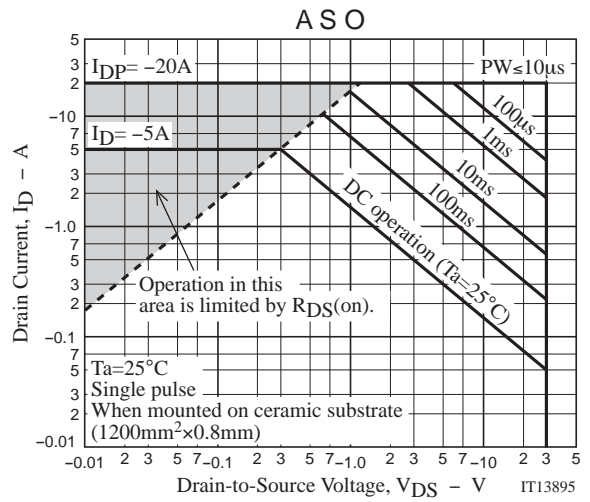
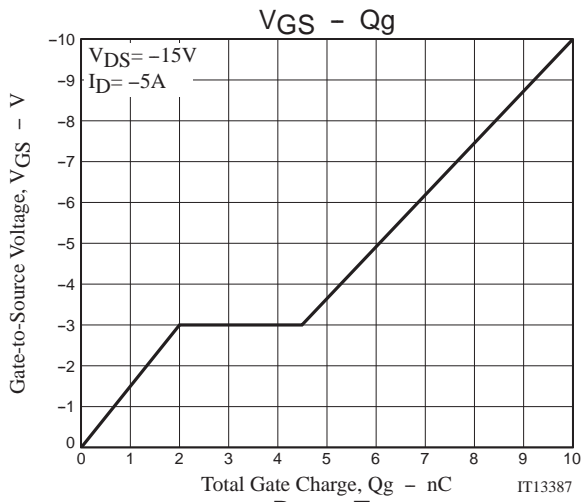
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
MCH6341-TL-E	MCPH6	3,000pcs./reel	Pb Free
MCH6341-TL-H	MCPH6	3,000pcs./reel	Pb Free and Halogen Free





MCH6341

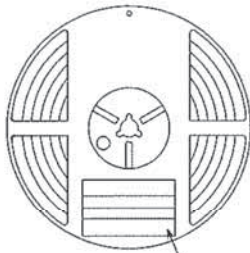
Taping Specification

MCH6341-TL-E, MCH6341-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
MCPH6	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

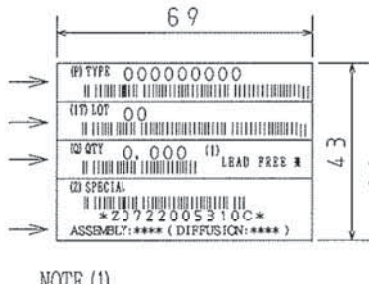
Packing method



Type No.
LOT No.
Quantity
Origin

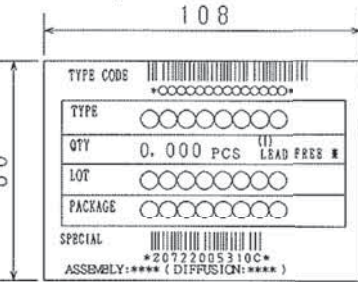
Reel label

Reel label, Inner box label
(unit:mm)



Outer box label

(It is a label at the time of factory shipments. The form of a label may change in physical distribution process.)



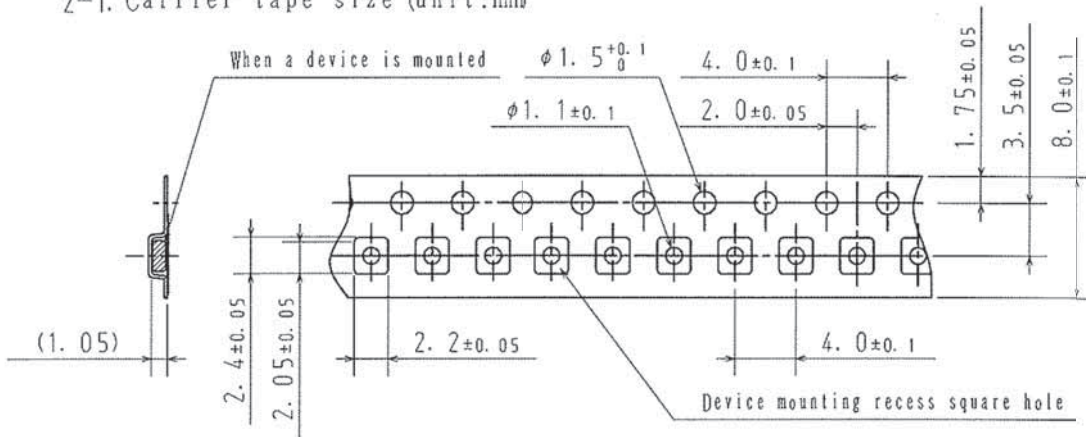
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

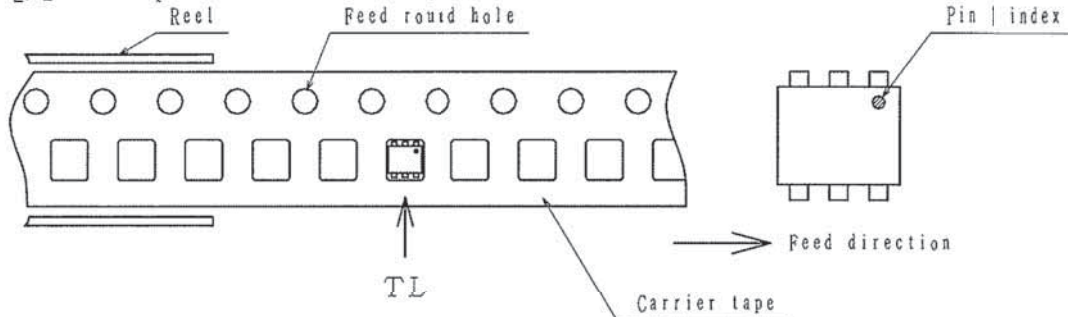
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

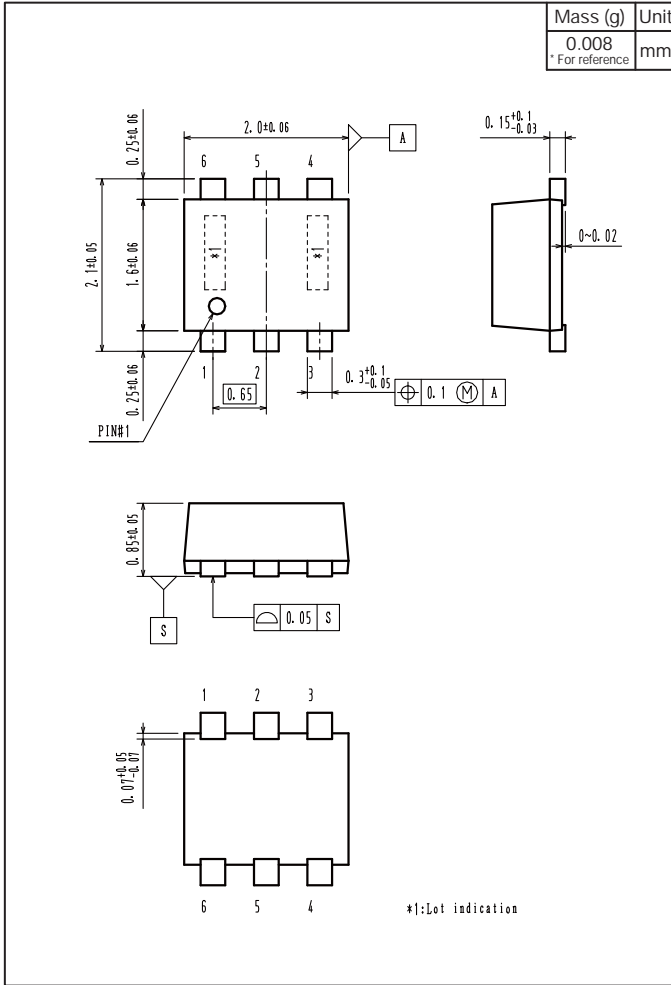


Those with pin | index on the feed hole side.....TL

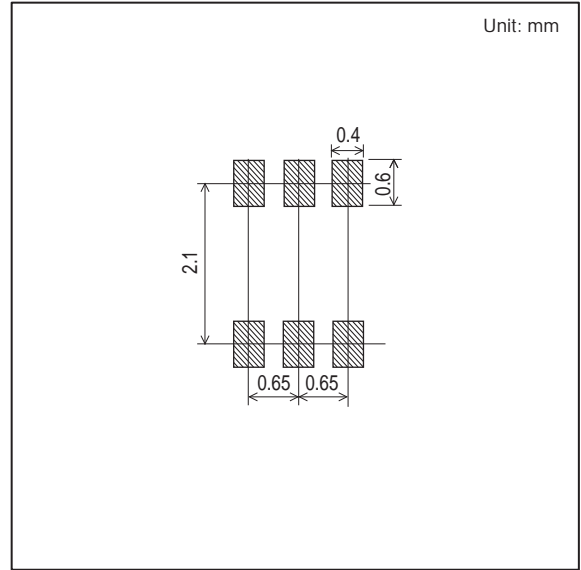
MCH6341

Outline Drawing

MCH6341-TL-E, MCH6341-TL-H



Land Pattern Example



Note on usage : Since the MCH6341 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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